DIODE MODULE (F.R.D.)

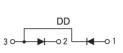
DD250GB

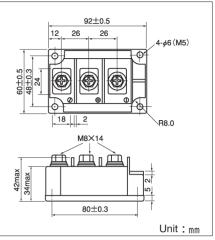
UL;E76102 (M)

Power Diode Module DD250GB series are designed for various rectifier circuits. DD250GB has two diode chips connected in series in a package and the mounting base is electrically isolated from elements for simple heatsink construction. Wide voltage rating up to 800V is available for various input voltage.

- Isolated mounting base
- •Two elements in a package for simple (single and three phase) bridge connections
- Highly reliable glass passivated chips
- High surge current capability (Applications)

Various rectifiers, Bettery chargers, DC motor drives





TOP

Maximum Ratings

Maximum Ratings						
Symbol	Symbol	Ratings				
		DD250GB40	DD250GB80	Unit		
VRRM	Repetitive Peak Reverse Voltage	400	800	V		
VRSM	Non-Repetitive Peak Reverse Voltage	480	960	V		

Symbol	Sy	Symbol Conditions		Ratings	Unit
IF (AV)	Average Forward Current		Single phase, half wave, 180° C conduction, Tc : 98° C	250	Α
IF (RMS)	R.M.S. Forward Current		Single phase, half wave, 180 $^\circ\!\mathrm{C}$ conduction, Tc : 98 $^\circ\!\mathrm{C}$	390	Α
IFSM	Surge Forward Current		¹ / ₂ cycle, 50/60Hz, peak value, non-repetitive	5000/5500	Α
l²t	l²t		Value for one cycle of surge current	125000	A ² S
Tj	Operating Junction Temperature			-40~+150	°C
Tstg	Storage Temperature			-40~+125	°C
Viso	Isolation Breakdown Voltage (R.M.S.)		A.C. 1 minute	2500	V
	Mounting Torque	Mounting (M5)	Recommended Value 1.5~2.5 (15~25)	2.7 (28)	N∙m
		Terminal (M8)	Recommended Value 8.8~10 (90~105)	11 (115)	(kgf•cm)
	Mass		Typical Value	510	g

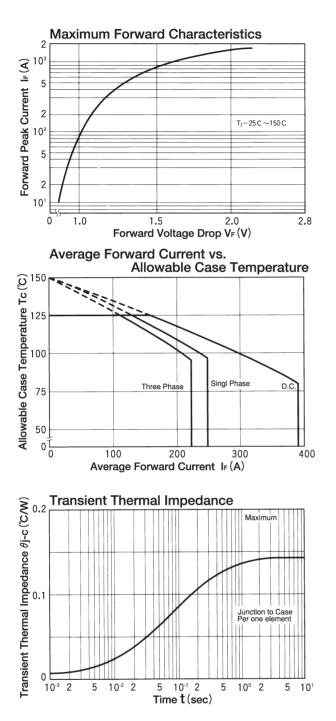
Electrical Characteristics

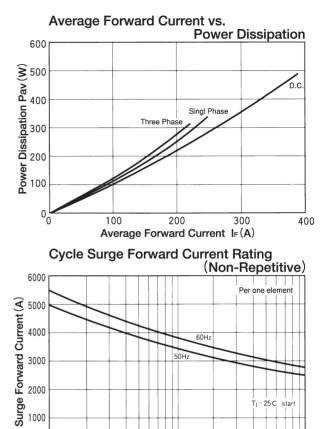
Symbol	Symbol	Conditions	Ratings			Unit
		Conditions		Тур.	Max.	Unit
IRRM	Repetitive Peak Reverse Current	Тј=150℃ at Vввм			50	mA
Vfm	Forward Voltage Drop	Тј=25℃, Iгм=750А, Inst. measurement			1.45	V
Rth (j-c)	Thermal Impedance	Junction to case			0.14	°C/W



0 ∟ 10°

2





10' Time (Cycles)

2

5

25 C star

5

10²